



# INTERNATIONAL SEMICONDUCTOR, INC.

**SUPER FAST RECOVERY, GLASS PASSIVATED, PLASTIC RECTIFIERS**

**VOLTAGE - 50 TO 800 Volts**

**CURRENT - 1.0 Ampere**

**SF11  
thru  
SF19**

## FEATURES

- Plastic Package carries Underwriters Laboratory Flammability Classification 94V-0
- Low cost construction utilizing void-free transfer molding technique
- Typical Recovery 35 nanoseconds
- Diffused, Glass Passivated Junction
- Low Leakage
- High Current Capability
- Easily cleaned with Freon, Alcohol, Chloroethane, and similar solvents
- High temperature soldering guaranteed: 265°C/10 seconds/.375"(9.5mm) lead lengths at 5 lbs(2.3kg) tension

## MECHANICAL DATA

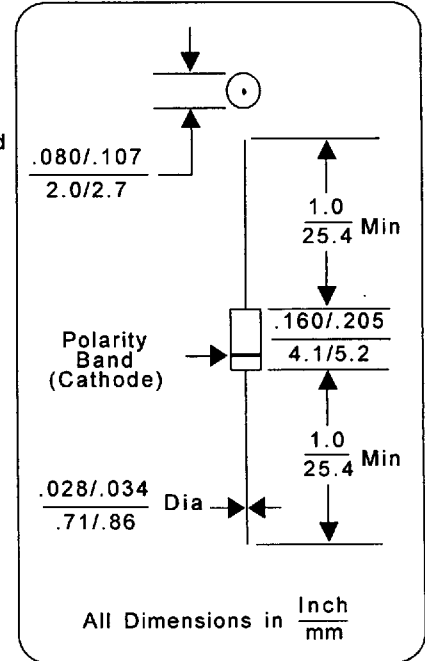
**Case:** JEDEC DO-41, molded plastic case

**TERMINALS:** Plated axial leads, solderable per MIL-S-202, Method 208

**WEIGHT:** 0.012 ounce, 0.3 gram

**MOUNTING POSITION:** Any

**HANDLING PRECAUTIONS:** None



**DO-41**

## MAXIMUM RATINGS AND ELECTRICAL CHARACTERISTICS

Ratings at 25°C ambient temperature unless otherwise specified  
Single phase, half wave, 60 Hz, resistive or inductive load  
For capacitive load, derate current by 20%

	SYMBOL	SF11	SF12	SF13	SF14	SF16	SF18	SF19	UNITS
Maximum Recurrent Peak Reverse Voltage	$V_{RRM}$	50	100	150	200	400	600	800	V
Maximum RMS Input Voltage	$V_{RMS}$	35	70	105	140	280	420	560	V
Maximum DC Blocking Voltage	$V_{DC}$	50	100	150	200	400	600	800	V
Maximum Average Forward Rectified Current at $T_c = 55^\circ\text{C}$	$I_{(AV)}$	1.0							A
Maximum Forward Surge Current 8.3 ms single half sine wave superimposed on rated load	$I_{FSM}$	30.0							A
Maximum Instantaneous Forward Voltage at 1.0A	$V_F$	0.975				1.250			V
Maximum DC Reverse Current at Rated $T_j=25^\circ\text{C}$ DC Blocking Voltage $T_j=125^\circ\text{C}$	$I_R$ $I_R$	5.0				100			ua ua
Maximum Reverse Recovery (Note 1)	$T_{RR}$	30				50	60		ns
Typ Junction Capacitance $T_j=25^\circ\text{C}$ (Note 2)	$C_j$	10.0				2.5	5.5		pf
Typical Thermal Resistance (Note 3)	$R_{\theta JA}$	41.0							$^\circ\text{C/W}$
Operating Temperature Range	$T_j$	-50 to +150							$^\circ\text{C}$
Storage Temperature Range	$T_{STG}$	-50 to +150							$^\circ\text{C}$

Note 1:  $T_{RR}$  Test Conditions:  $I_F=0.5A$ ,  $I_R=1.0A$ ,  $I_{RR}=0.25A$

Note 2: Measured at 1.0 MHz and 10.0 Volt Bias Voltage

Note 3: Thermal Resistance from Junction to Ambient at .375"(9.5mm) lead lengths, P.C. Board mounted

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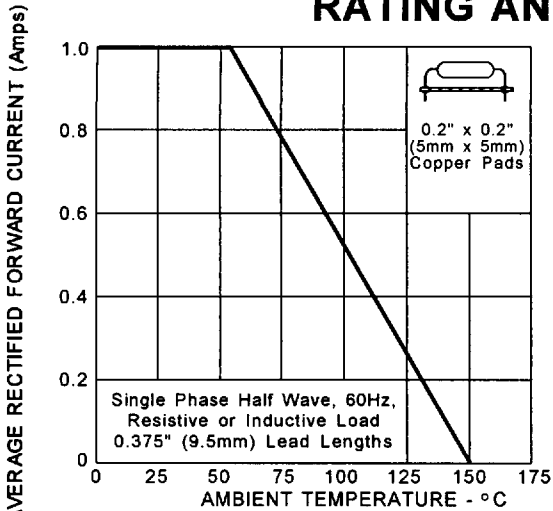
■ 9000378 0000917 028 ■

Fax: (908) 245-5541

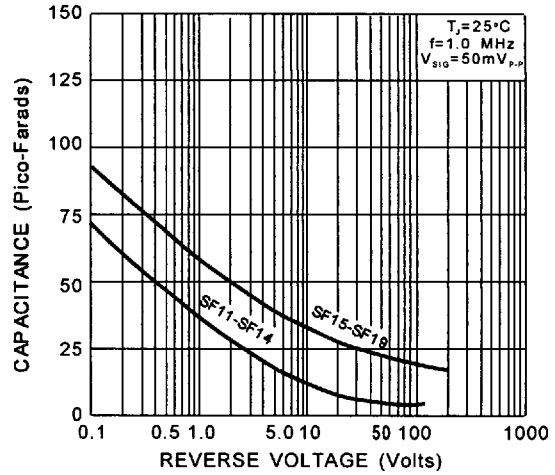
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# SF11 thru SF19

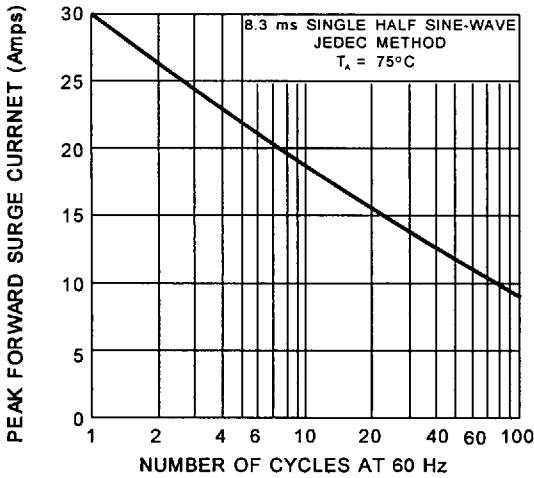
## RATING AND CHARACTERISTIC CURVES



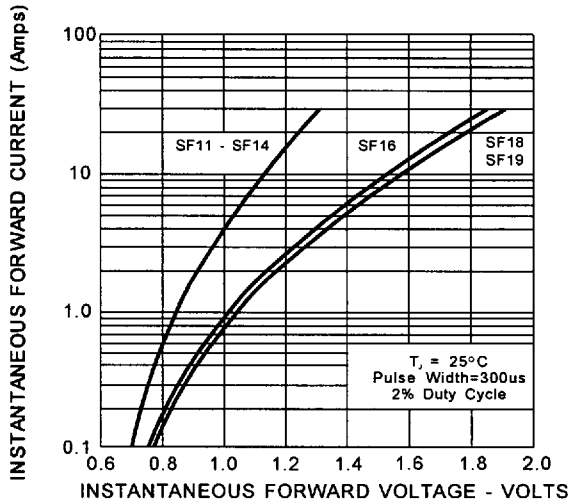
**FIG. 2 - FORWARD CURRENT DERATING CURVE**



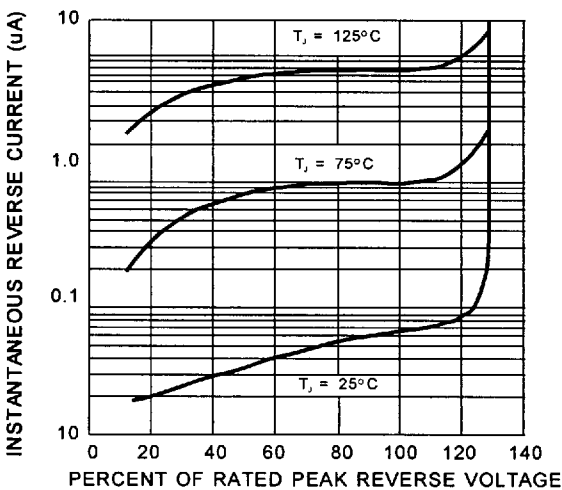
**FIG. 3 - TYPICAL JUNCTION CAPACITANCE**



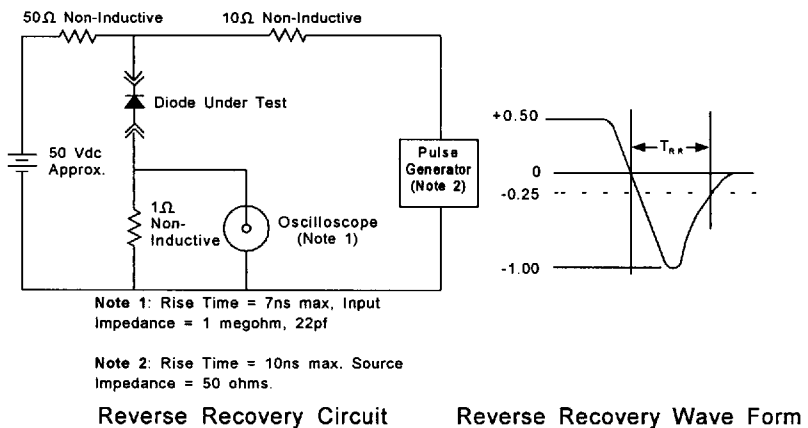
**FIG. 4 - MAXIMUM NON-REPETITIVE SURGE CURRENT**



**FIG. 5 TYPICAL FORWARD CHARACTERISTICS**



**FIG. 6 TYPICAL REVERSE CHARACTERISTICS**



**Fig. 7 - REVERSE RECOVERY TIME CHARACTERISTIC AND TEST CIRCUIT DIAGRAM**

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